Erratum: Oxidation-enhanced annealing of implantation-induced Z_{1/2} centers in 4H-SiC: Reaction kinetics and modeling [Phys. Rev. B 86, 075205 (2012)]

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There are three errors in the numbering of references in this manuscript. On page 4, right column, first paragraph, Ref. 30 should be Ref. 33 (Song et al.). On page 6, left column, second paragraph, Ref. 33 should be Ref. 36 (Bockstedte et al.) and the same applies to the last reference in this paragraph. This does not affect the conclusions of the manuscript, nor any other aspect of the work.